

# LET9045F

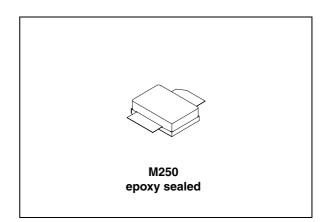
### RF power transistor from the LdmoST family of n-channel enhancement-mode lateral MOSFETs

### Features

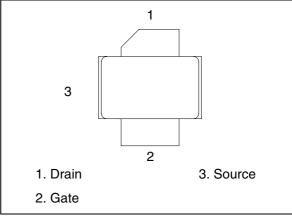
- Excellent thermal stability
- Common source configuration
- POUT = 45 W with 18.5 dB gain @ 960 MHz
- BeO free package
- In compliance with the 2002/95/EC european directive

### Description

The LET9045F is a common source n-channel enhancement-mode lateral field-effect RF power transistor designed for broadband commercial and industrial applications at frequencies up to 1.0 GHz. The LET9045F is designed for high gain and broadband performance operating in common source mode at 28 V. It is ideal for base station applications requiring high linearity.







#### Table 1. Device summary

Order code	Package	Branding
LET9045F	M250	LET9045F

## 1 Maximum ratings

	Absolute maximum ratings (TCASE = 23°C)		
Symbol	Parameter	Value	Unit
V <sub>(BR)DSS</sub>	Drain-source voltage	80	V
V <sub>GS</sub>	Gate-source voltage	-0.5 to +15	V
۱ <sub>D</sub>	Drain current	9	А
P <sub>DISS</sub>	Power dissipation (@ $T_C = 70 \ ^{\circ}C$ )	108	W
TJ	Max. operating junction temperature	200	°C
T <sub>STG</sub>	Storage temperature	-65 to +150	°C

#### Table 2. Absolute maximum ratings ( $T_{CASE} = 25 \ ^{\circ}C$ )

	Table 3.	Thermal	data
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Sym	nbol	Parameter	Value	Unit
R <sub>th</sub>	(JC)	Junction-case thermal resistance	1.2	°C/W



## 2 Electrical characteristics

T<sub>C</sub> = 25 °C

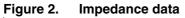
#### Table 4. Static

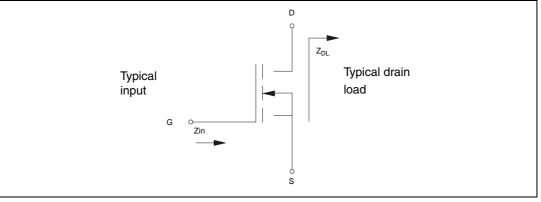
Symbol	Test conditions	Min.	Тур.	Max.	Unit
V <sub>(BR)DSS</sub>	$V_{GS}$ = 0 V; I <sub>DS</sub> = 10 mA	80			V
I <sub>DSS</sub>	$V_{GS} = 0 V; V_{DS} = 28 V$			1	μA
I <sub>GSS</sub>	$V_{GS} = 20 \text{ V}; \text{ V}_{DS} = 0 \text{ V}$			1	μA
V <sub>GS(Q)</sub>	$V_{DS} = 28 \text{ V}; \text{ I}_{D} = 300 \text{ mA}$	2.0		5.0	V
V <sub>DS(ON)</sub>	$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 3 \text{ A}$		0.9	1.2	V
G <sub>FS</sub>	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 3 A	2.5			mho
C <sub>ISS</sub>	$V_{GS} = 0 \text{ V}; \text{ V}_{DS} = 28 \text{ V}; \text{ f} = 1 \text{ MHz}$		58		pF
C <sub>OSS</sub>	$V_{GS} = 0 \text{ V}; \text{ V}_{DS} = 28 \text{ V}; \text{ f} = 1 \text{ MHz}$		29		pF
C <sub>RSS</sub>	$V_{GS} = 0 V; V_{DS} = 28 V; f = 1 MHz$		0.8		pF

Symbol	Test conditions	Min.	Тур.	Max.	Unit
P <sub>OUT</sub>	$V_{DD}$ = 28 V; $I_{DQ}$ = 300 mA; $P_{IN}$ = 1 W; f = 960 MHz	45	59		W
G <sub>PS</sub>	$V_{DD}$ = 28 V; $I_{DQ}$ = 300 mA; $P_{IN}$ = 1 W; f = 960 MHz	16.5	17.7		dB
h <sub>D</sub>	$V_{DD}$ = 28 V; $I_{DQ}$ = 300 mA; $P_{IN}$ = 1 W; f = 960 MHz	60	65		%
Load mismatch	$V_{DD}$ = 28 V; $I_{DQ}$ = 300 mA; $P_{IN}$ = 1 W; f = 960 MHz All phase angles	10:1			VSWR



## 3 Impedance data



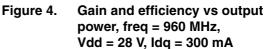


#### Table 6.Impedance data

Frequency	Z <sub>IN</sub> (Ω)	<b>Ζ<sub>DL</sub> (</b> Ω <b>)</b>
920	0.8 - j 0.08	5.3 + j 0.63
945	0.7 - j 0.4	5 + j 1.5
960	0.6 - j 0.6	4.7 + j 2

### 4 Typical performances

Figure 3. Gain vs output power and bias F current, freq = 960 MHz, Vdd = 28 V



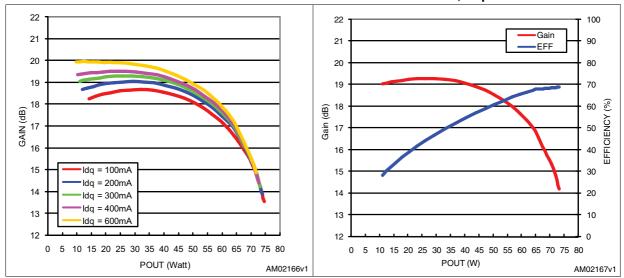
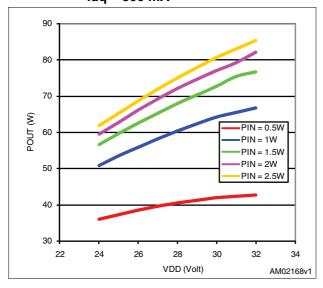
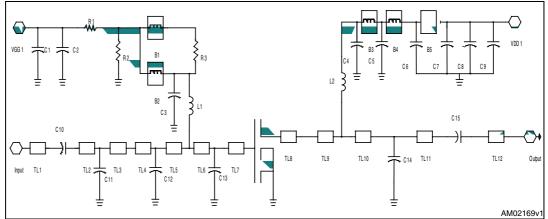


Table 7.Output power vs supply voltage<br/>freq = 960 MHz, Vdd = 28 V,<br/>Idq = 300 mA



## 5 Test circuit





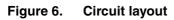
Item	Qty	Part number	Vendor	Description		
R1, R2	2	CR1206-8W-112JB	VENKEL	1.1 k $\Omega$ 1/8W surface mount chip resistor		
R3	1	CR1206-8W-100JB	VENKEL	10 $\Omega$ 1/8W surface mount chip resistor		
Coil	2		BELDEN	Inductor 5 turns air WOUND#20AWG ID =0.130 in (3.3 mm) bylon coated		
B1,B2,B 3,B4,B5	5	2743021447	FAIR-RITE CORP	Surface mount EMI sheild bead		
C1,C7, C8	3	T491D106K035AT	Kemet	10 µF 35 V tantalum capacitors		
C2	1			100 µF 63 V electrolytic capacitor		
C3, C4, C10, C15	4	ATC100B470XXXX	ATC	47 pF chip capacitor		
C5, C6	2	ATC200B393MW	ATC	39000 pF chip capacitor		
C9	1			330 uF 50 V electrolytic capacitor		
C11, C13, C14	3	27291PC	Johanson	0.8-8 pF giga trim variable capacitor		
C12	1	ATC100B110XXXX	ATC	11 pF chip capacitor		
TL1				L = 1.350in [34.29 mm] W = 0.082in [02.08 mm]		
TL2				L = 0.144in [3.65 mm] W = 0.082in [02.08 mm]		
TL3				L = 0.311in [7.91 mm] W = 0.082in [02.08 mm]		
TL4				L = 00.82in [2.09 mm] W = 0.323in [08.21 mm]		
TL5				L = 0.194 in [4.94 mm] W = 0.323in [08.21 mm]		

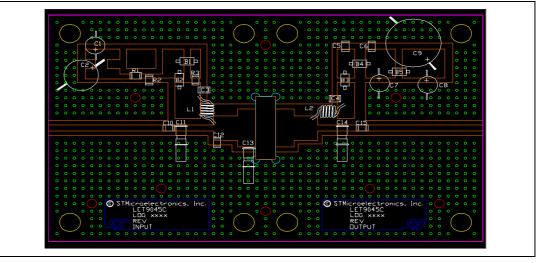
### Table 8. LET9045F components list



Item	Qty	Part number	Vendor	Description	
TL6				L = 0.059in [1.49 mm] W= 0.506in [12.85 mm]	
TL7				L = 0.144in [3.65 mm] W = 0.506in [12.85 mm]	
TL8				L = 0.208in [5.28 mm] W = 0.506in [12.85 mm]	
TL9				L = 0.275in [6.98 mm] W = 0.323in [08.21 mm]	
TL10				L = 0.210in [5.33 mm] W = 0.082in [02.08 mm]	
TL11				L = 0.260in [6.60 mm] W = 0.082in [02.08 mm]	
TL12				L = 1.350in [34.29 mm] W = 0.082in [02.08 mm]	
Board 3X5	1		Rogers corp	Er=2.55 t=0.0026in h=0.030in	

Table 8. LET9045F components list (continued)







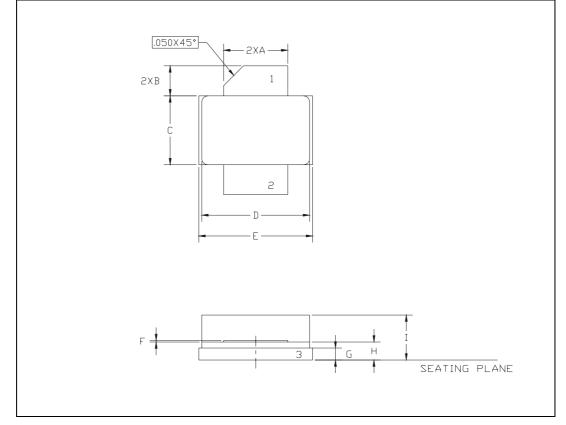
### 6 Package mechanical data

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Dim.		mm.			Inch	
	Min	Тур	Max	Min	Тур	Max
А	5.21		5.71	0.205		0.225
В	2.16		2.92	0.085		0.115
С	5.59		6.09	0.220		0.240
D	8.89		9.40	0.350		0.370
E	9.40		9.91	0.370		0.390
F	0.11		0.15	0.004		0.006
G	0.89		1.14	0.035		0.045
Н	1.45		1.70	0.057		0.067
I	2.67		3.94	0.105		0.155

Table 9.M250 (.230 x .360 2L N/HERM W/FLG) mechanical data

### Figure 7. Package dimensions





## 7 Revision history

Table 10.Document revision history

Date	Revision	Changes	
02-Nov-2009	1	Initial release.	
11-Feb-2010	2	Changed test condition for V <sub>(BR)DSS</sub> in <i>Table 4: Static</i> .	



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